



# BUK9K13-60E

Dual N-channel 60 V, 12.5 mΩ logic level MOSFET

2 September 2015

Product data sheet

## 1. General description

Dual logic level N-channel MOSFET in an LFAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Quick reference data

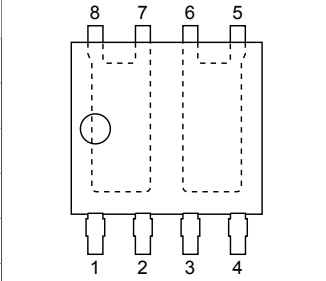
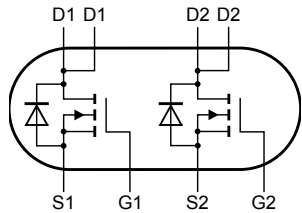
| Symbol                                       | Parameter                        | Conditions   |     | Min | Typ | Max  | Unit |
|--|----------------------------------|--|-----|-----|-----|------|------|
| $V_{DS}$                                     | drain-source voltage             | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$  |     | -   | -   | 60   | V    |
| $I_D$  | drain current                    | $V_{GS} = 5\text{ V}; T_{mb} = 25\text{ °C};$ <a href="#">Fig. 2</a>   | [1] | -   | -   | 40   | A    |
| $P_{tot}$                                    | total power dissipation          | $T_{mb} = 25\text{ °C};$ <a href="#">Fig. 1</a>  |     | -   | -   | 64   | W    |
| <b>Static characteristics FET1 and FET2</b>  |                                  |  |     |     |     |      |      |
| $R_{DSon}$                                   | drain-source on-state resistance | $V_{GS} = 5\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C};$ <a href="#">Fig. 11</a>  |     | -   | 10  | 12.5 | mΩ   |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |  |     |     |     |      |      |
| $Q_{GD}$                                     | gate-drain charge                | $I_D = 10\text{ A}; V_{DS} = 48\text{ V}; V_{GS} = 5\text{ V};$<br>$T_j = 25\text{ °C};$ <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |     | -   | 7.9 | -    | nC   |

[1] Continuous current is limited by package

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## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline  | Graphic symbol  |
|-----|--------|-------------|---|---|
| 1   | S1     | source1     |  <p>LFPAK56D (SOT1205)</p> |  <p>mbk725</p> |
| 2   | G1     | gate1       |   |   |
| 3   | S2     | source2     |   |   |
| 4   | G2     | gate2       |   |   |
| 5   | D2     | drain2      |   |   |
| 6   | D2     | drain2      |   |   |
| 7   | D1     | drain1      |   |   |
| 8   | D1     | drain1      |   |   |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |
|-------------|----------|--|---------|
|             | Name     | Description  | Version |
| BUK9K13-60E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK9K13-60E | 91360E       |

## 8. Limiting values

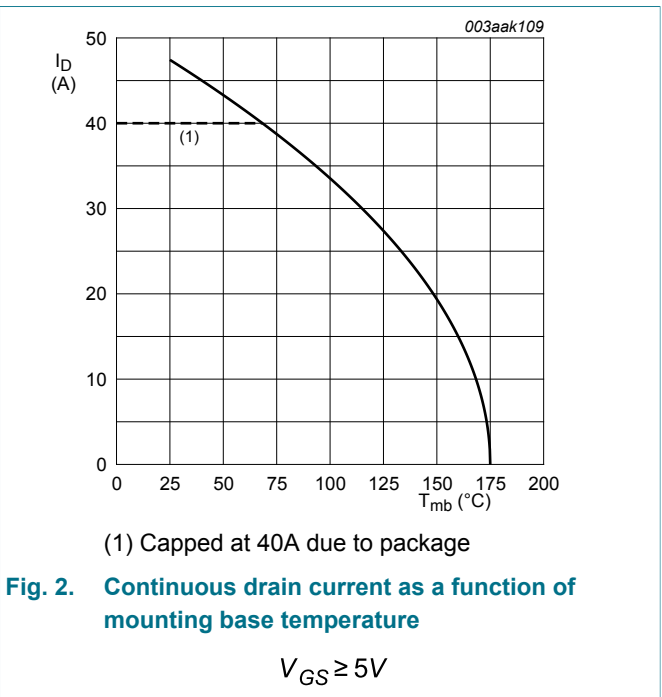
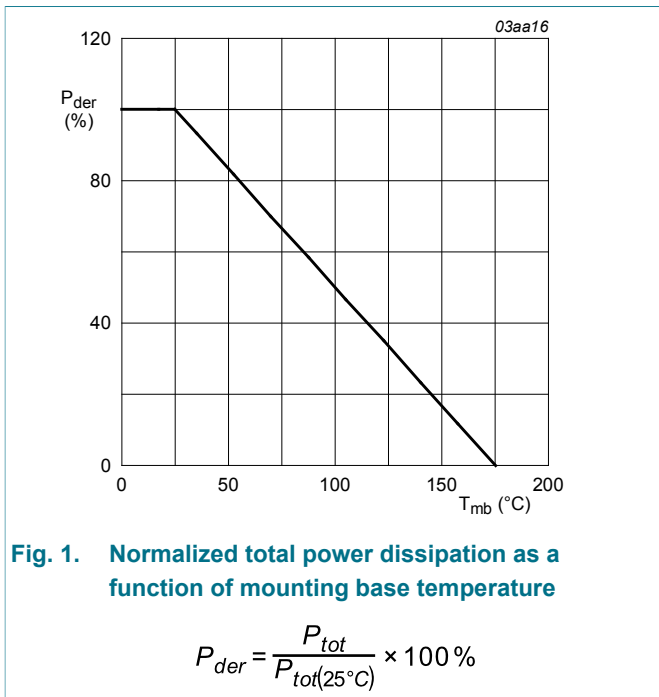
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions  | Min    | Max | Unit |
|-----------|-------------------------|---|--------|-----|------|
| $V_{DS}$  | drain-source voltage    | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$        | -      | 60  | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                              | -      | 60  | V    |
| $V_{GS}$  | gate-source voltage     | $T_j \leq 175\text{ °C}$ ; DC                             | -10    | 10  | V    |
|           |                         | $T_j \leq 175\text{ °C}$ ; Pulsed                         | [1][2] | 15  | V    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C}$ ; Fig. 1                          | -      | 64  | W    |
| $I_D$     | drain current           | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 2  | [3]    | 40  | A    |
|           |                         | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 2 |        | 33  | A    |

| Symbol                                    | Parameter                                    | Conditions   | Min                    | Max | Unit |    |
|---|--|--|------------------------|-----|------|----|
| $I_{DM}$                                  | peak drain current                           | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 3</a>  | -                      | 190 | A    |    |
| $T_{stg}$                                 | storage temperature                          |  | -55                    | 175 | °C   |    |
| $T_j$                                     | junction temperature                         |  | -55                    | 175 | °C   |    |
| $T_{sld(M)}$                              | peak soldering temperature                   |  | -                      | 260 | °C   |    |
| <b>Source-drain diode FET1 and FET2</b>   |  |  |                        |     |      |    |
| $I_S$                                     | source current                               | $T_{mb} = 25\text{ °C}$  | <a href="#">[3]</a>    | -   | 40   | A  |
| $I_{SM}$                                  | peak source current                          | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$   |                        | -   | 190  | A  |
| <b>Avalanche Ruggedness FET1 and FET2</b> |  |  |                        |     |      |    |
| $E_{DS(AL)S}$                             | non-repetitive drain-source avalanche energy | $I_D = 40\text{ A}$ ; $V_{sup} \leq 60\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ;<br>$V_{GS} = 5\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; unclamped;<br><a href="#">Fig. 4</a> | <a href="#">[4][5]</a> | -   | 82   | mJ |

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering  $T_j$  and or  $V_{GS}$ .
- [3] Continuous current is limited by package
- [4] Refer to application note AN10273 for further information
- [5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



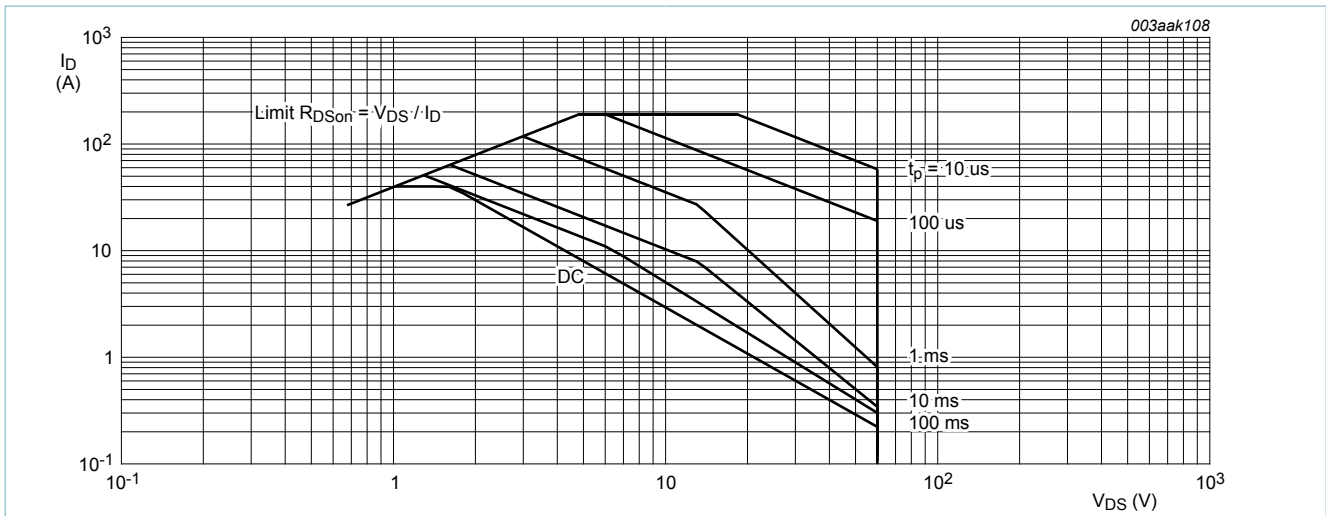


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^\circ C$ ;  $I_{DM}$  is a single pulse

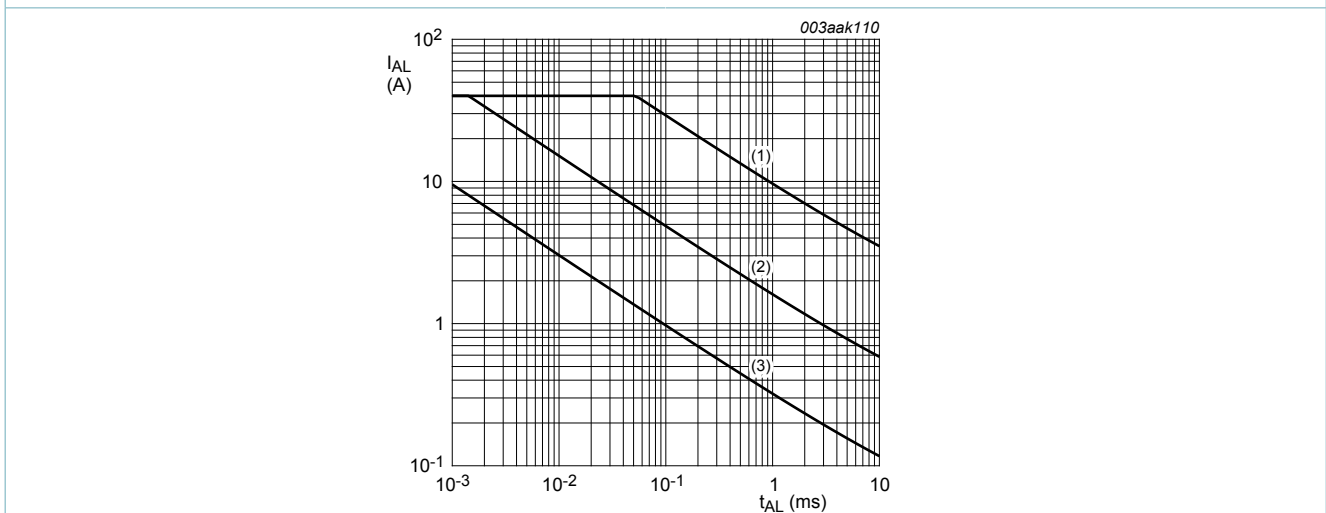


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j(init)} = 25^\circ C$ ; (2)  $T_{j(init)} = 150^\circ C$ ; (3) Repetitive Avalanche

## 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions  | Min | Typ | Max  | Unit |
|----------------|---|---|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5  | -   | -   | 2.36 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 95  | -    | K/W  |

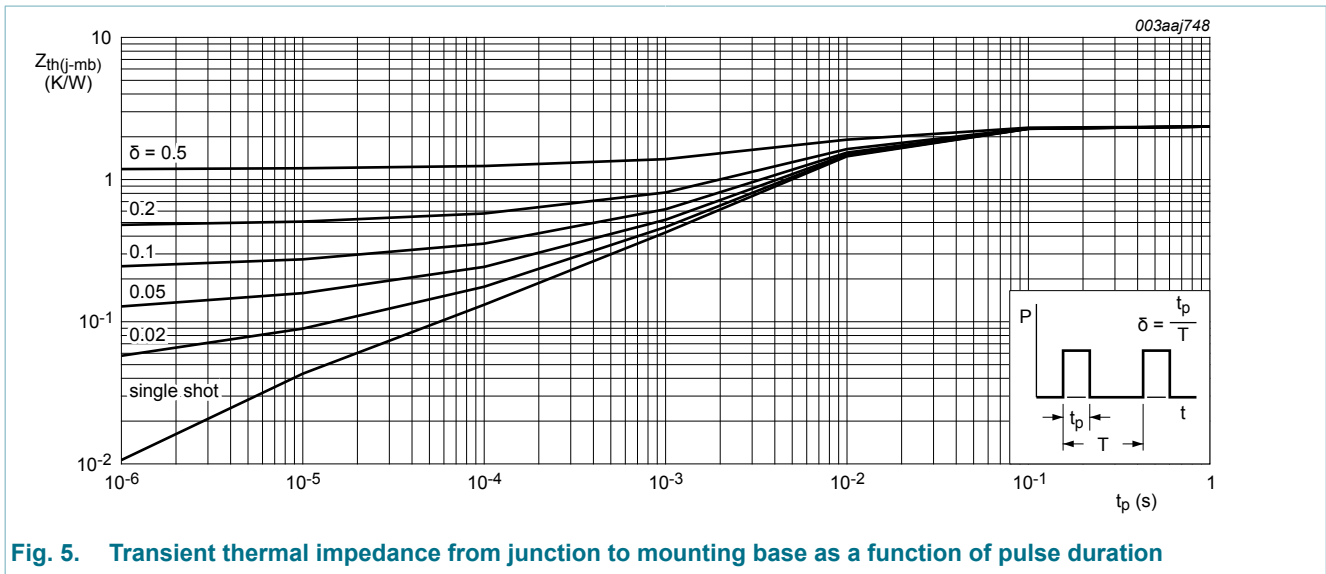


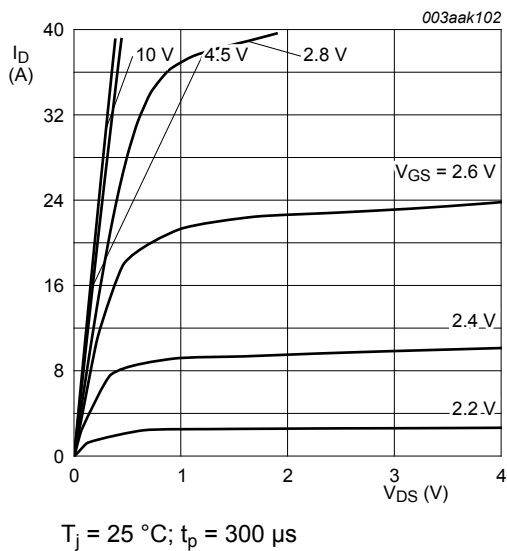
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

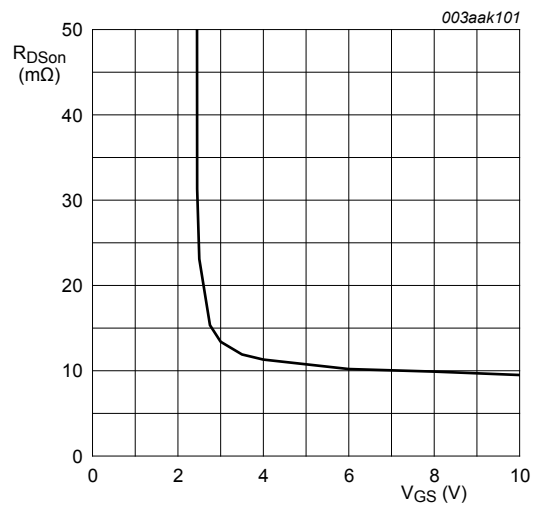
Table 7. Characteristics

| Symbol                                       | Parameter                        | Conditions  | Min | Typ  | Max  | Unit    |
|--|----------------------------------|---|-----|------|------|---------|
| <b>Static characteristics FET1 and FET2</b>  |                                  |   |     |      |      |         |
| $V_{(BR)DSS}$                                | drain-source breakdown voltage   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$   | 54  | -    | -    | V       |
|  |                                  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$  | 60  | -    | -    | V       |
| $V_{GS(th)}$                                 | gate-source threshold voltage    | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$<br><a href="#">Fig. 9; Fig. 10</a>                                | 1.4 | 1.7  | 2.1  | V       |
|  |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$<br><a href="#">Fig. 9</a>  | 0.5 | -    | -    | V       |
|  |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$<br><a href="#">Fig. 9</a>  | -   | -    | 2.45 | V       |
| $I_{DSS}$                                    | drain leakage current            | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$  | -   | 0.02 | 1    | $\mu A$ |
|  |                                  | $V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$   | -   | -    | 500  | $\mu A$ |
| $I_{GSS}$                                    | gate leakage current             | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$   | -   | 2    | 100  | nA      |
|  |                                  | $V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$  | -   | 2    | 100  | nA      |
| $R_{DSon}$                                   | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 11</a>                                      | -   | 10   | 12.5 | mΩ      |
|  |                                  | $V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ }^\circ C;$<br><a href="#">Fig. 11; Fig. 12</a>                         | -   | 22   | 28.3 | mΩ      |
|  |                                  | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ C;$<br><a href="#">Fig. 11</a>                                  | -   | 9    | 11.2 | mΩ      |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |   |     |      |      |         |
| $Q_{G(tot)}$                                 | total gate charge                | $I_D = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 5 \text{ V};$<br>$T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 13; Fig. 14</a> | -   | 22.4 | -    | nC      |
| $Q_{GS}$                                     | gate-source charge               |   | -   | 5.2  | -    | nC      |

| Symbol                                  | Parameter                    | Conditions  | Min | Typ  | Max  | Unit |
|---|------------------------------|---|-----|------|------|------|
| $Q_{GD}$                                | gate-drain charge            |   | -   | 7.9  | -    | nC   |
| $C_{iss}$                               | input capacitance            | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>              | -   | 2215 | 2953 | pF   |
| $C_{oss}$                               | output capacitance           |   | -   | 225  | 270  | pF   |
| $C_{rss}$                               | reverse transfer capacitance |   | -   | 116  | 159  | pF   |
| $t_{d(on)}$                             | turn-on delay time           | $V_{DS} = 48\text{ V}; R_L = 5\text{ }^\Omega; V_{GS} = 5\text{ V}; R_{G(ext)} = 5\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$  | -   | 13   | -    | ns   |
| $t_r$                                   | rise time                    |   | -   | 22.1 | -    | ns   |
| $t_{d(off)}$                            | turn-off delay time          |   | -   | 30.5 | -    | ns   |
| $t_f$                                   | fall time                    |   | -   | 21.8 | -    | ns   |
| <b>Source-drain diode FET1 and FET2</b> |                              |   |     |      |      |      |
| $V_{SD}$                                | source-drain voltage         | $I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 16</a>                                   | -   | 0.8  | 1.2  | V    |
| $t_{rr}$                                | reverse recovery time        | $I_S = 10\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 30\text{ V}; T_j = 25\text{ }^\circ\text{C}$ | -   | 22.7 | -    | ns   |
| $Q_r$                                   | recovered charge             |   | -   | 18.9 | -    | nC   |



**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$

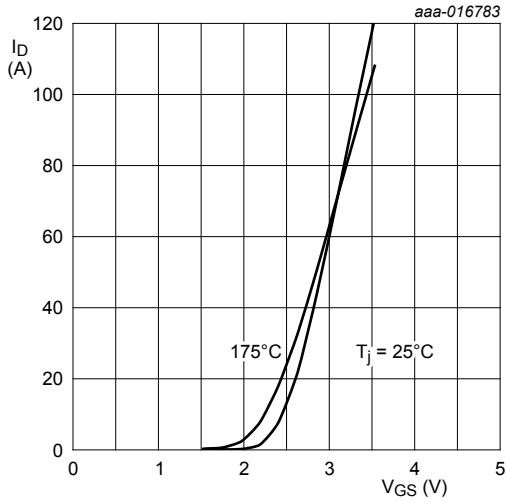


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

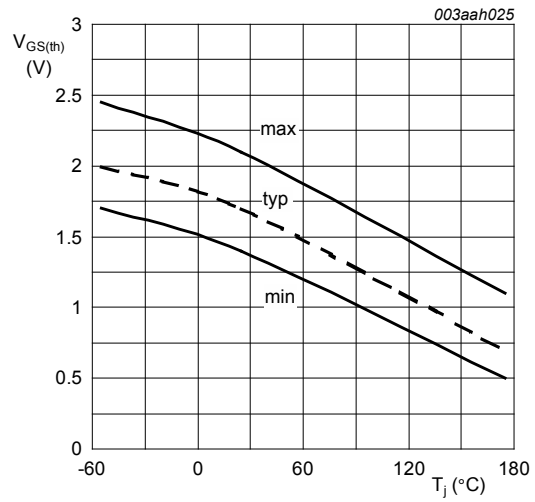


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}$ ;  $V_{DS} = V_{GS}$

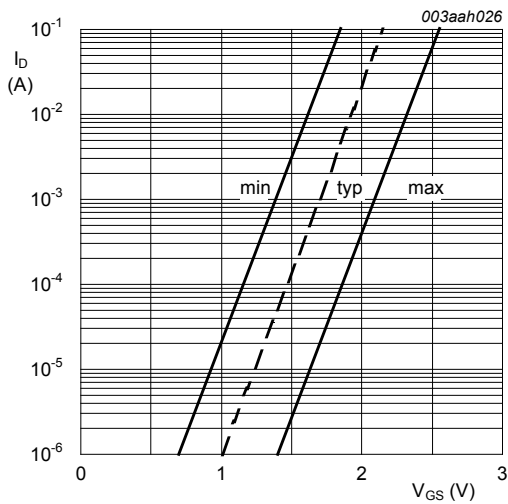


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}$ ;  $V_{DS} = 5\text{V}$

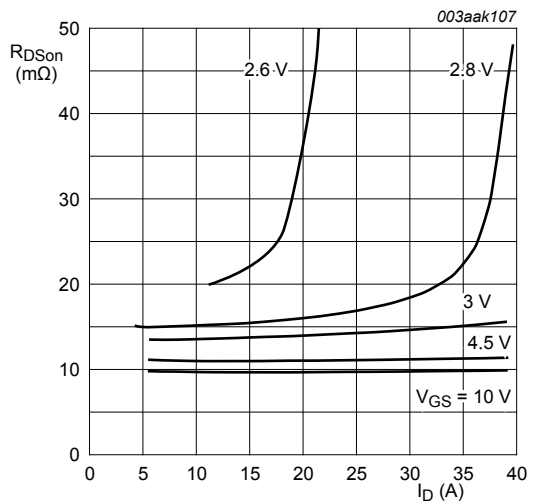


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

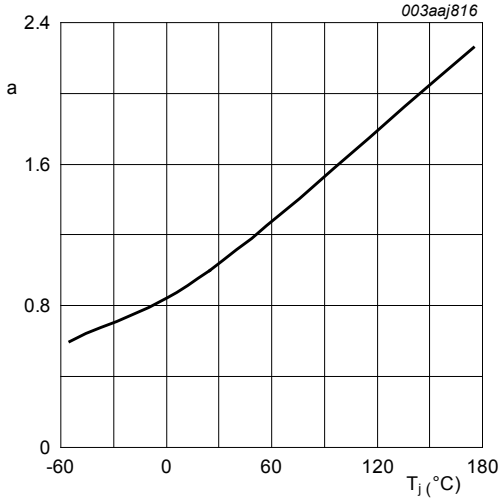


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

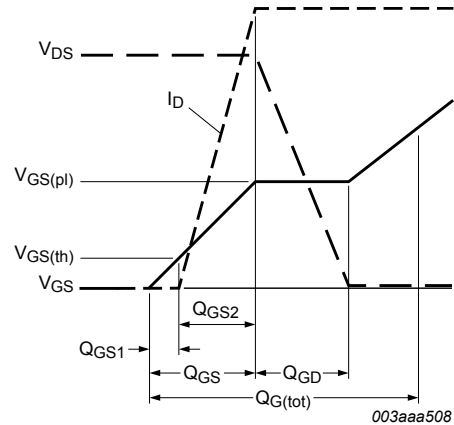


Fig. 13. Gate charge waveform definitions

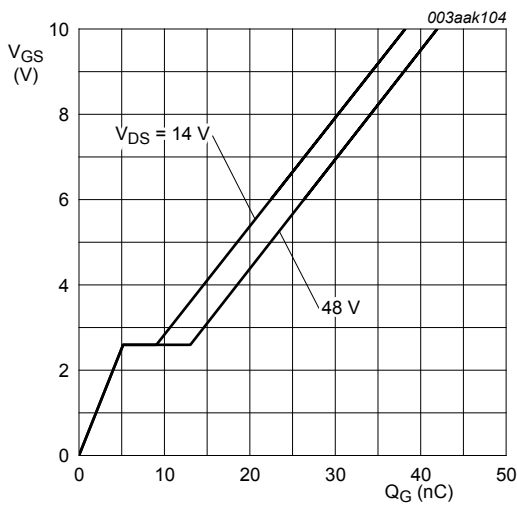


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 10\text{A}$$

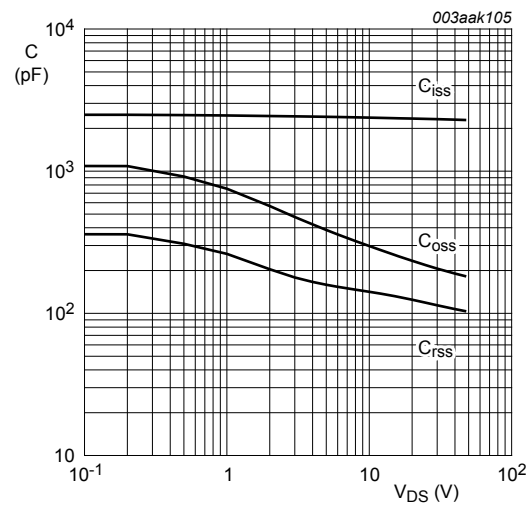
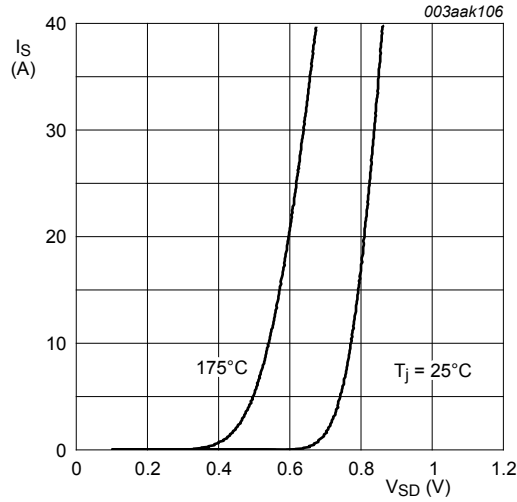


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

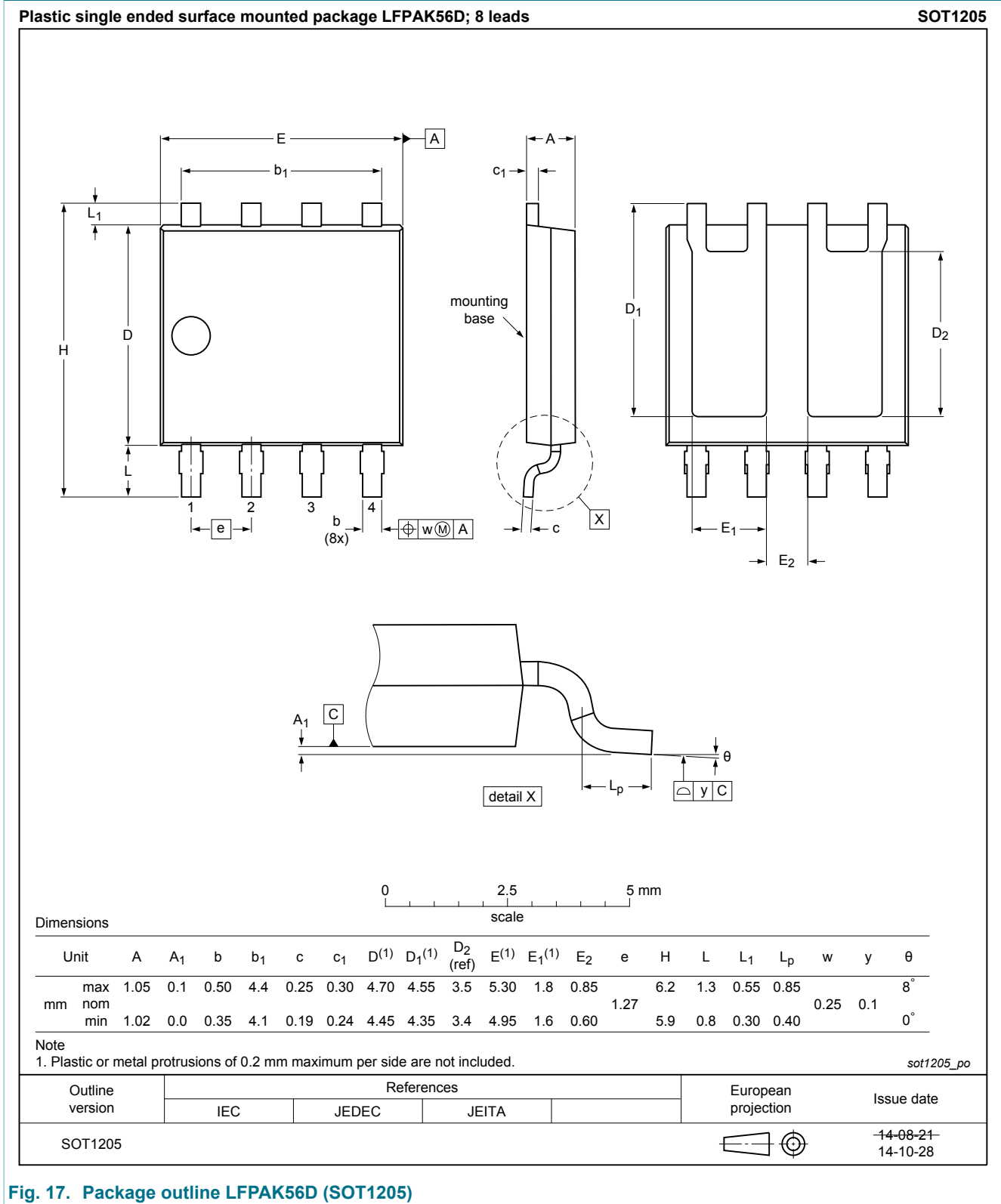




**Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

$$V_{GS} = 0V$$

### 11. Package outline



**Fig. 17. Package outline LFPAK56D (SOT1205)**

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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